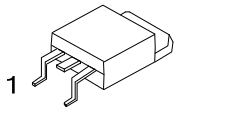
-60V, -30A P-CHANNEL POWER MOSFET



TO-252

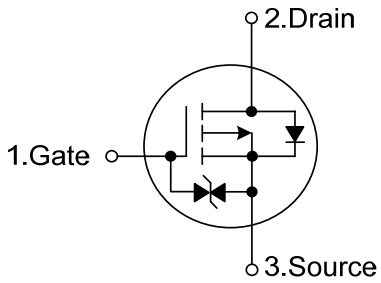
■ DESCRIPTION

The UTC **UT30P06Z** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed, cost-effectiveness and a minimum on-state resistance. It can also withstand high energy in the avalanche.

■ FEATURES

* $R_{DS(ON)} \leq 58\ m\Omega$ @ V_{GS}= -10V, I_D= -15A
* $R_{DS(ON)} \leq 92\ m\Omega$ @ V_{GS}= -4.5V, I_D= -15A
* High Switching Speed
* With ESD Protected

■ SYMBOL



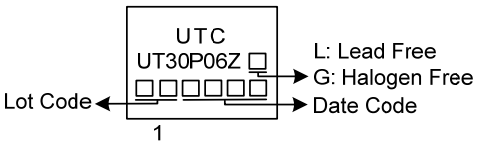
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT30P06ZL-TN3-R	UT30P06ZG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT30P06ZG-TN3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current	Continuous, V_{GSS}@-10V	T_C=25°C	I_D	-30	A
	Pulsed (Note 2)		I_{DM}	-60	A
Avalanche Energy	Repetitive (Note 3)		E_{AS}	25.5	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	3.1	V/ns
Power Dissipation (T_C=25°C)			P_D	44	W
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 0.1mH, I_{AS} = -22.6A, V_{DD} = -50V, R_G = 25Ω, Starting T_J=25°C.
4. I_{SD} ≤ -30A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.84 (Note)	°C/W

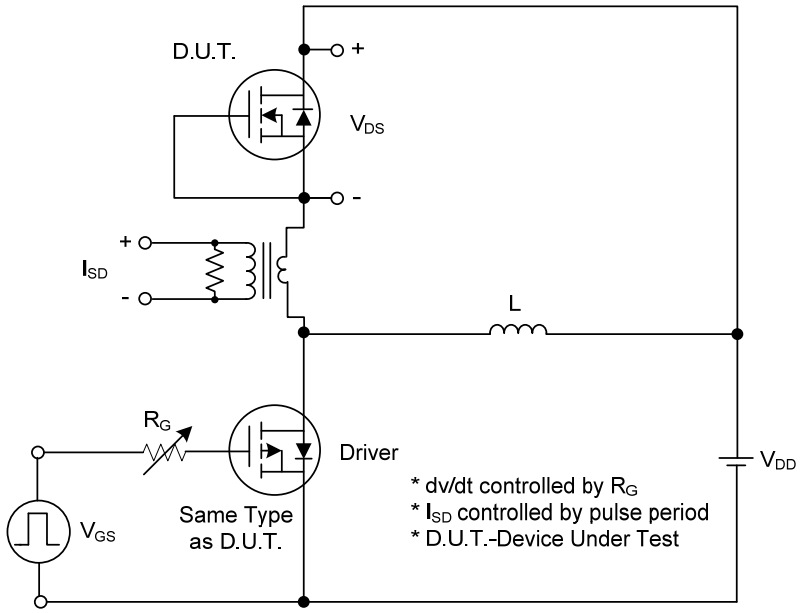
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

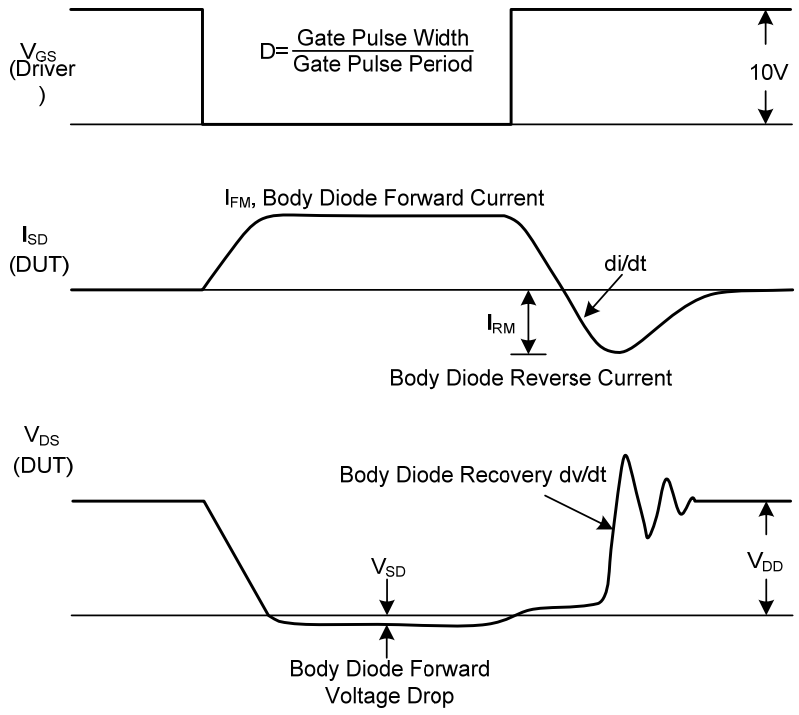
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=-250μA, V_{GS}=0V	-60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=-60V, V_{GS}=0V,			-1	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+10	uA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-10	uA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.0		-3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=-10V, I_D=-15A			58	mΩ
			V_{GS}=-4.5V, I_D=-15A			92	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=-25V, V_{GS}=0V, f=1.0MHz		1911		pF
Output Capacitance		C_{OSS}			131		pF
Reverse Transfer Capacitance		C_{RSS}			100		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=-48V, V_{GS}=-10V, I_D=-30A (Note 1, 2)		48		nC
Gate-Source Charge		Q_{GS}			8		nC
Gate-Drain Charge		Q_{GD}			16		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=-30V, V_{GS}=-10V, I_D=-30A, R_G=3Ω (Note 1, 2)		16		ns
Rise Time		t_R			26		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			257		ns
Fall-Time		t_F			87		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				-30	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=-30A, V_{GS}=0V (Note 2)			-1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S=-30A, V_{GS}=0V, dI$_F$/dt=100A/μs		62		ns
Body Diode Reverse Recovery Charge		Q_{rr}			72		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

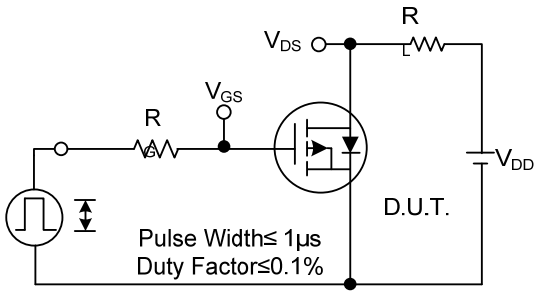


Peak Diode Recovery dv/dt Test Circuit

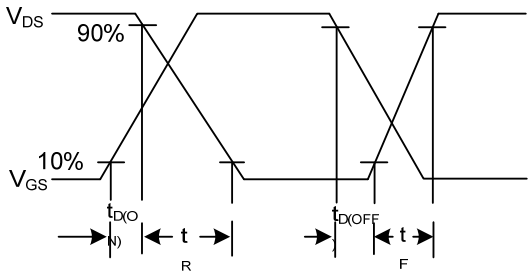


Peak Diode Recovery dv/dt Waveforms

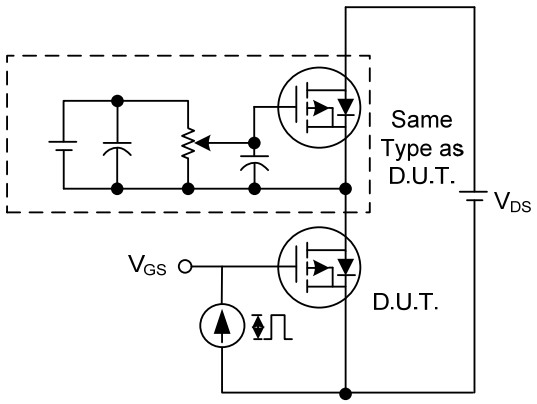
■ TEST CIRCUITS AND WAVEFORMS



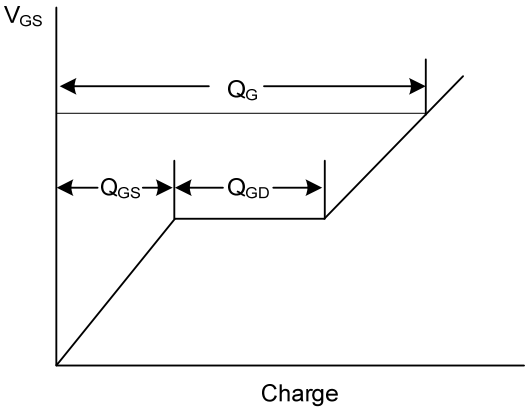
Switching Test Circuit



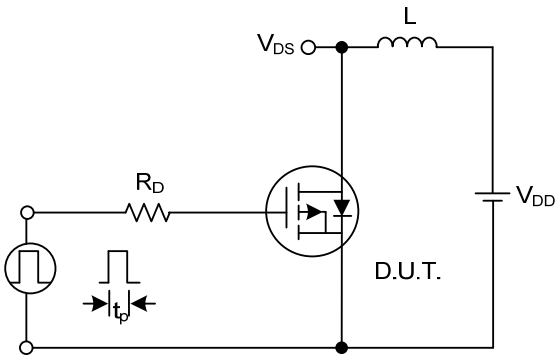
Switching Waveforms



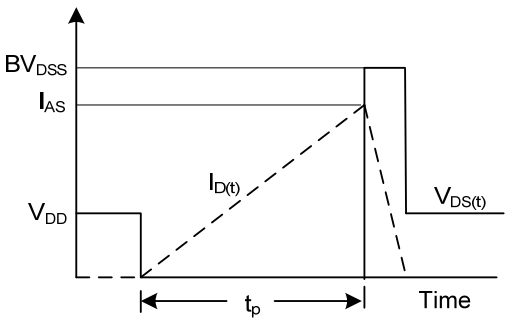
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms